

LNA2W01L

GaAs Infrared Light Emitting Diode

For optical control systems

Features

- High-power output, high-efficiency : $P_O = 4.5$ mW (typ.)
- Emitted light spectrum suited for silicon photodetectors
- Infrared light emission close to monochromatic light :
 $\lambda_p = 950$ nm (typ.)
- Narrow directivity : $\theta = 18$ deg. (typ.)
- Ultra-miniature double ended package

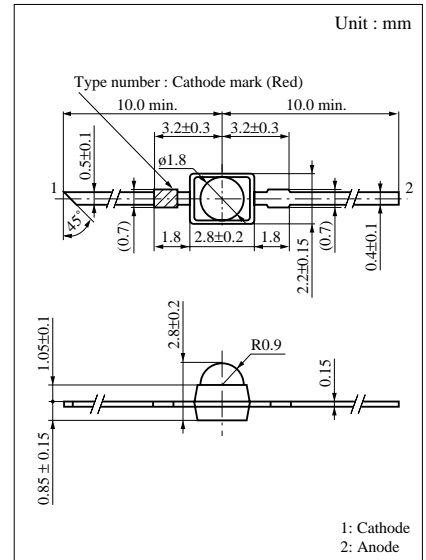
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

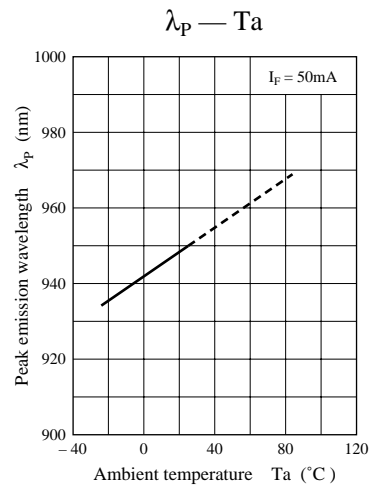
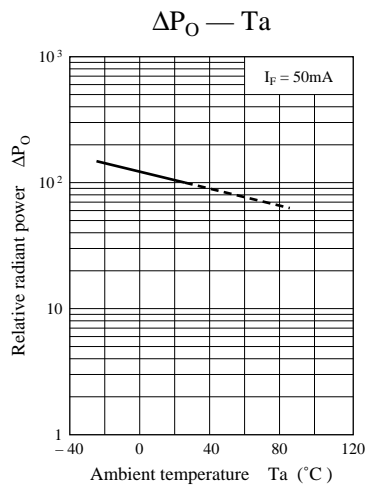
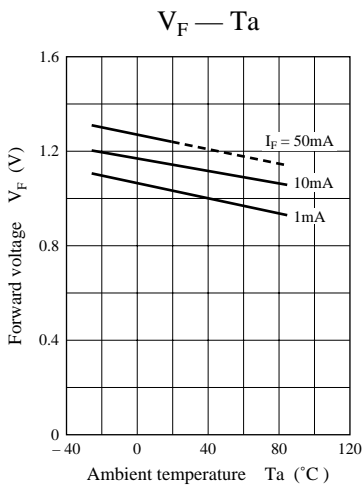
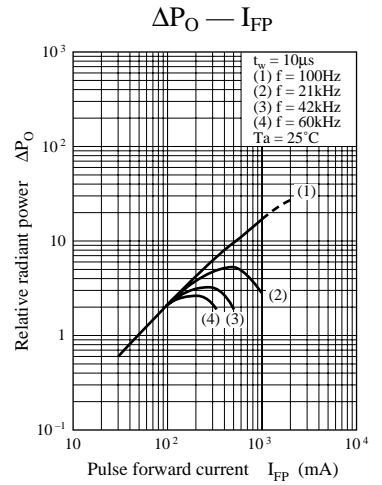
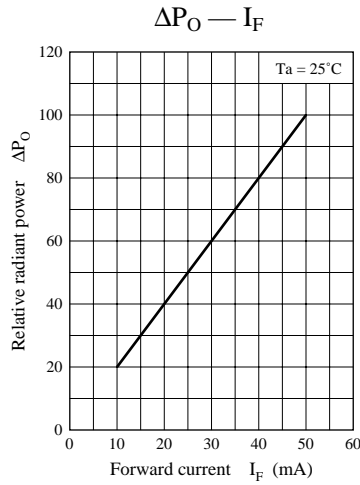
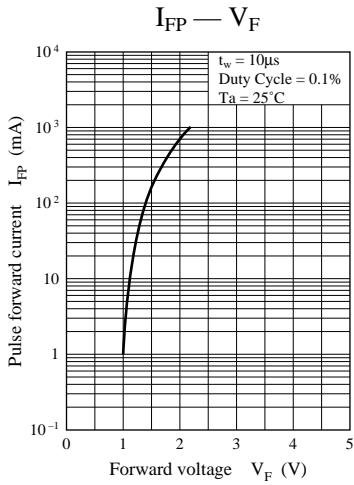
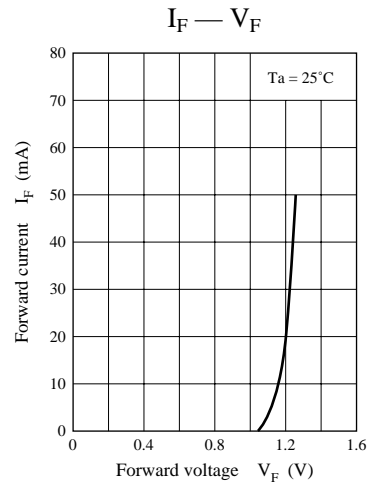
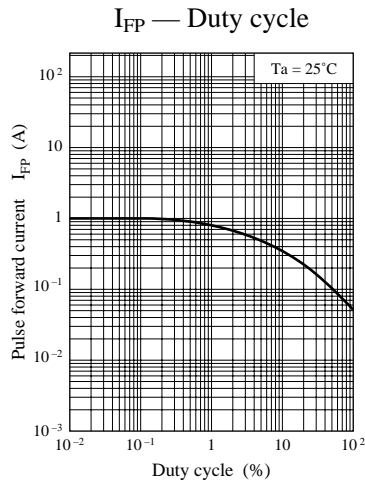
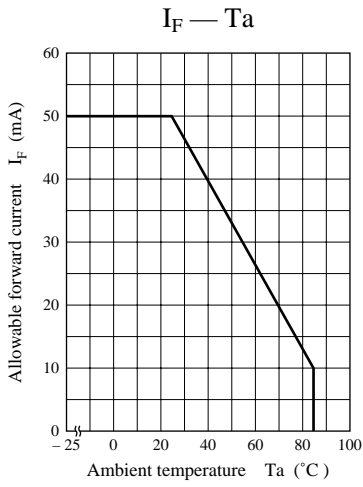
Parameter	Symbol	Rated	Unit
Power dissipation	P_D	75	mW
Forward current (DC)	I_F	50	mA
Pulse forward current	I_{FP}^*	1	A
Reverse voltage (DC)	V_R	3	V
Operating ambient temperature	T_{opr}	-25 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-30 to +100	$^\circ\text{C}$

* $f = 100$ Hz, Duty cycle = 0.1 %

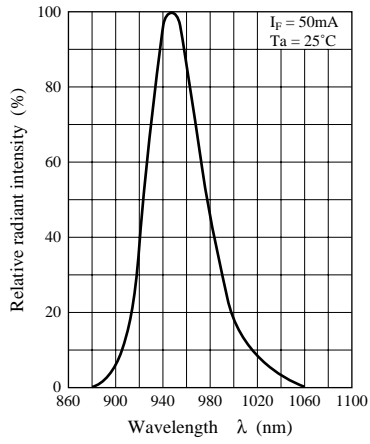
Electro-Optical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Radiant power	P_O	$I_F = 50\text{mA}$	3	4.5		mW
Peak emission wavelength	λ_p	$I_F = 50\text{mA}$		950		nm
Spectral half band width	$\Delta\lambda$	$I_F = 50\text{mA}$		50		nm
Forward voltage (DC)	V_F	$I_F = 50\text{mA}$		1.25	1.5	V
Reverse current (DC)	I_R	$V_R = 3\text{V}$			10	μA
Capacitance between pins	C_t	$V_R = 0\text{V}$, $f = 1\text{MHz}$		35		pF
Half-power angle	θ	The angle in which radiant intensity is 50%		18		deg.

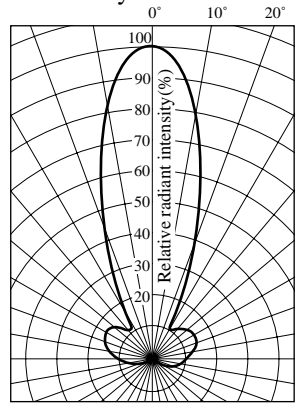




Spectral characteristics



Directivity characteristics



Frequency characteristics

